

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph [00056] with the following paragraph:

[00056] Then, as shown in FIG. 5B, on the substrate having the gate line, etc. are sequentially formed an insulating layer 510, a semiconductor layer [[512]] 511, an impurity semiconductor layer [[511]] 512, and a second metal layer [[512]] 514. The insulating layer 510 is formed with inorganic insulating material such as silicon nitride (SiN_x) or silicon dioxide (SiO_2), or organic insulating material such as benzocyclobutene (BCB) or acryl group resin. The semiconductor layer [[512]] 511 is formed with intrinsic semiconductor material such as purely amorphous silicon. The impurity semiconductor layer [[511]] 512 is formed with semiconductor material having N^+ or P^+ impurities. The second metal layer [[512]] 514 is formed with the metal having high melting point such as molybdenum (Mo), tantalum (Ta), tungsten (W), or antimony (Sb).